FABRICATION METHOD OF WIRING SUBSTRATE FOR MOUNTING SEMICONDUCTOR ELEMENT AND SEMICONDUCTOR DEVICE

ABSTRACT OF THE DISCLOSURE

By adopting an electrolytic plating method in forming the bump 6, the drawbacks of the conventional electrolytic plating method should be avoided. For example, the necessity of adopting a lead wiring for each wiring or the like should be eliminated. On the surface of a metal base (1), a resist film (first resist film) (4) having a negative pattern for forming a wiring film and a resist film (second resist film) (5) having a negative pattern for forming the bump or the pad is formed. By using these films as masks, electrolytic plating of a bump material film is conducted to form the bump (6). Subsequently, after only the second film (5) is removed. By using the first resist film (4) as a mask, electrolytic plating is then conducted to form a wiring film (7).

FIGURE 3C